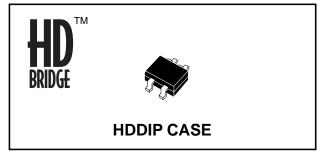
CBRHD SERIES

HIGH DENSITY SURFACE MOUNT 1/2 AMP DUAL IN LINE BRIDGE RECTIFIER





FEATURES:

- Truly efficient use of board space, requires only 42mm² of board space vs. 120mm² of board space for industry standard 1.0 Amp surface mount bridge rectifier.
- 50% higher density (amps/mm²) than the industry standard 1.0 Amp surface mount bridge rectifier.
- Glass passivated chips for high reliability.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHD series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

		CBRHD	CBRHD	CBRHD	CBRHD		
	SYMBOL	<u>-02</u>	<u>-04</u>	<u>-06</u>	<u>-10*</u>	UNITS	
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	1000	V	
DC Blocking Voltage	V_{R}	200	400	600	1000	V	
RMS Reverse Voltage	V _R (RMS)	140	280	420	700	V	
Average Forward Current (T _A =40°C)(1)	lo ` ´		0.5				
Average Forward Current (T _A =40°C)(2)	IO		0.8				
Peak Forward Surge Current	I _{FSM}		30				
Operating and Storage							
Junction Temperature	T_{J}, T_{stg}		-65 to +150				

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
٧ _F	I _F =400mA (Per Diode)			1.0	V
IR	V _R =Rated V _{RRM}			5.0	μΑ
I_{R}	V_R =Rated V_{RRM} , T_A =125°C			500	μΑ
$C_{,J}$	V_R =4.0V, f=1.0MHz		20		pF

- (1) Mounted on a Glass-Epoxy P.C.B.
- (2) Mounted on a Ceramic P.C.B.

^{*}Available on special order, please consult factory.

All dimensions in inches (mm).

TOP VIEW

